

LAPT

2SA1186

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2837)

Application : Audio and General Purpose

■ Absolute maximum ratings (Ta=25°C)

Symbol	2SA1186	Unit
VCBO	-150	V
VCEO	-150	V
VEBO	-5	V
IC	-10	A
IB	-2	A
Pc	100(Ta=25°C)	W
Tj	150	°C
Tstg	-55 to +150	°C

■ Electrical Characteristics (Ta=25°C)

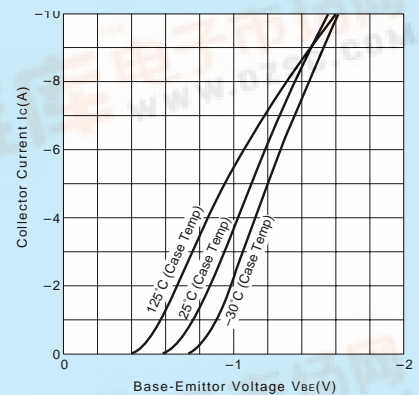
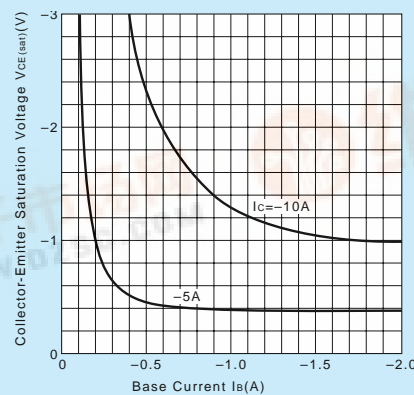
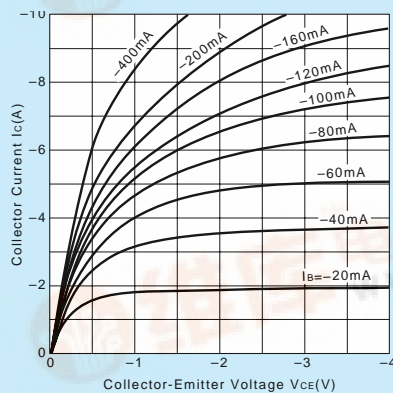
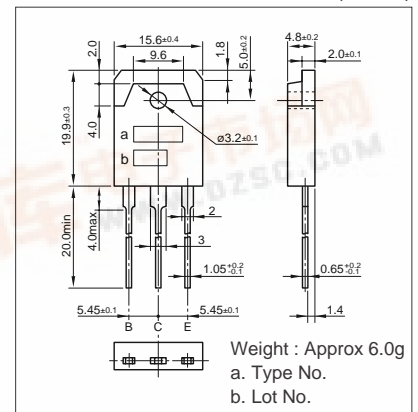
Symbol	Conditions	2SA1186	Unit
ICBO	VCB=-150V	-100max	μA
IEBO	VEB=-5V	-100max	μA
V(BR)CEO	IC=-25mA	-150min	V
hFE	VCE=-4V, IC=-3A	50min*	
VCE(sat)	IC=-5A, IB=-0.5A	-2.0max	V
fr	VCE=-12V, IE=1A	60typ	MHz
COB	VCB=-80V, f=1MHz	110typ	pF

*hFE Rank: O(50 to 100), P(70 to 140), Y(90 to 180)

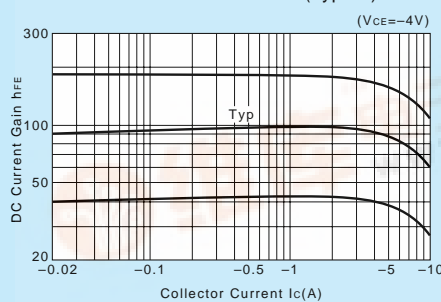
■ Typical Switching Characteristics (Common Emitter)

VCC (V)	RL (Ω)	IC (A)	VB2 (V)	IB1 (mA)	IB2 (mA)	ton (μs)	tstg (μs)	tf (μs)
-60	12	-5	5	-500	500	0.25typ	0.8typ	0.2typ

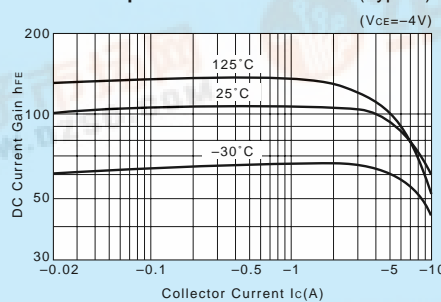
External Dimensions MT-100(TO3P)



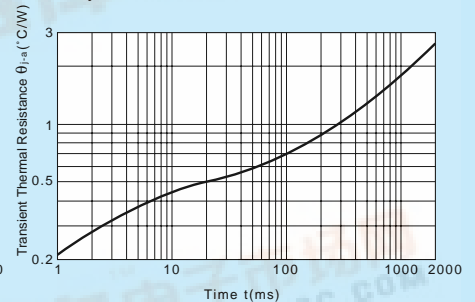
hFE-IC Characteristics (Typical)



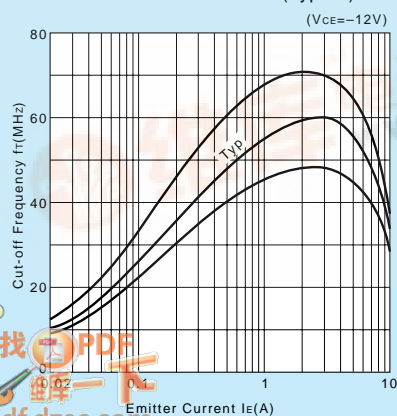
hFE-IC Temperature Characteristics (Typical)



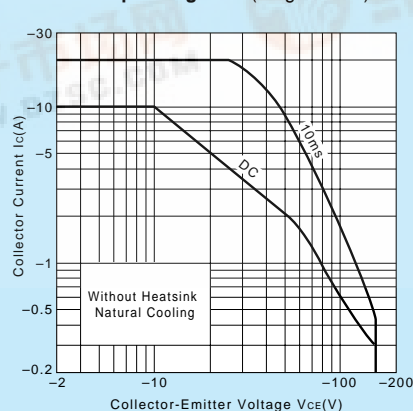
θJA-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

